CLAIMS

1. A method for measuring a DIC defect shape on a silicon wafer, comprising steps of:

detecting a DIC defect on a main surface of the silicon wafer with a particle counter;

specifying position coordinates of the detected DIC defect; and

measuring a shape including at least a height or depth of the detected DIC defect by utilizing the specified position coordinates according to phase-shifting interferometry, wherein

a width of the DIC defect is on the order of tens of micrometers to hundreds of micrometers.

2. The method for measuring a DIC defect shape according to claim 1, wherein the main surface of the silicon wafer is a surface on which a device is to be fabricated.

3. A method for polishing a silicon wafer, comprising:

setting a polishing removal amount based on the shape of the DIC defect measured by the method for measuring a DIC defect shape according to claim 1 or 2; and

polishing the silicon wafer.